

**isc Silicon NPN Power Transistor**
**BUS12A**
**DESCRIPTION**

- Collector–Emitter Sustaining Voltage  
:  $V_{CEO(SUS)} = 450V(\text{Min.})$
- High Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

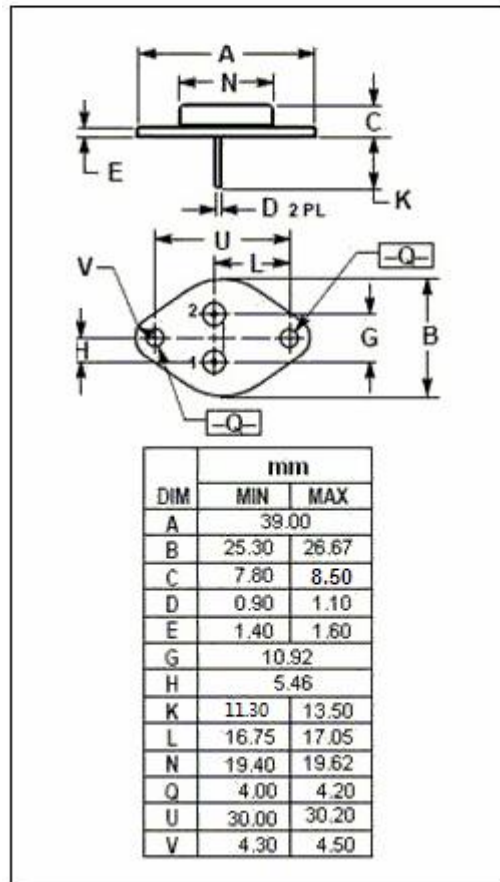
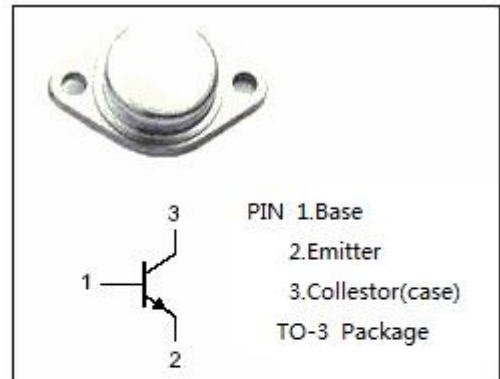
- Designed for use in converters, inverters, switching regulators, motor control systems etc.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector-Emitter Voltage	1000	V
$V_{CEO}$	Collector-Emitter Voltage	450	V
$V_{EBO}$	Emitter-Base Voltage	9	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-peak $t_p < 2\text{ms}$	20	A
$I_B$	Base Current-Continuous	4	A
$I_{BM}$	Base Current-peak $t_p < 2\text{ms}$	6	A
$P_C$	Collector Power Dissipation $T_C=25^\circ\text{C}$	125	W
$T_j$	Junction Temperature	200	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~200	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.4	$^\circ\text{C/W}$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub> =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	450			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> =V <sub>CESMmax</sub> ; V <sub>BE</sub> = 0 V <sub>CE</sub> = V <sub>CESMmax</sub> ; V <sub>BE</sub> = 0; T <sub>J</sub> = 125°C			1 3	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 9V; I <sub>C</sub> = 0			10	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	15		50	

Switching Times , Resistive Load

t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 5A ; I <sub>B1</sub> = -I <sub>B2</sub> = 1A			1.0	μs
t <sub>stg</sub>	Storage Time				4.0	μs
t <sub>f</sub>	Fall Time				0.8	μs

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